

isc Silicon NPN Darlington Power Transistor

TIP130

DESCRIPTION

- High DC Current Gain-
: $h_{FE} = 1000(\text{Min}) @ I_C = 4A$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(\text{SUS})} = 60V(\text{Min})$
- Low Collector-Emitter Saturation Voltage-
: $V_{CE(\text{sat})} = 2.0V(\text{Max}) @ I_C = 4A$
- Complement to Type TIP135

APPLICATIONS

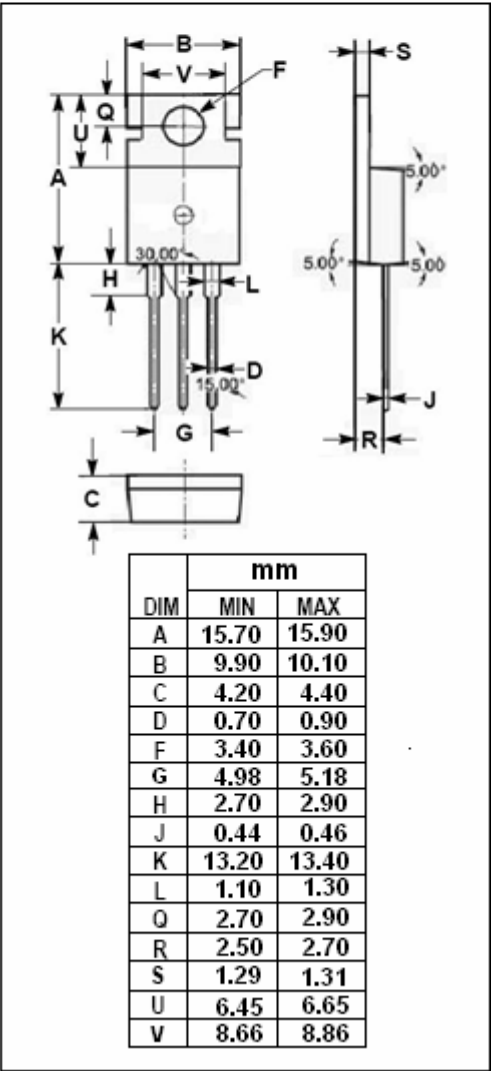
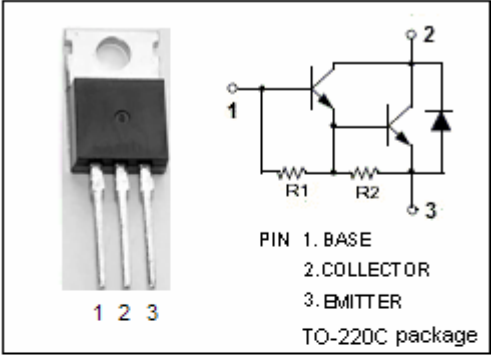
- Designed for general-purpose amplifier and low-speed switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	8	A
I_{CM}	Collector Current-Peak	12	A
I_B	Base Current- Continuous	0.3	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	70	W
	Collector Power Dissipation @ $T_a=25^{\circ}\text{C}$	2	
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.785	$^{\circ}\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	63.5	$^{\circ}\text{C/W}$



isc Silicon NPN Darlington Power Transistor**TIP130****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 30mA, I _B = 0	60		V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 16mA		2.0	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 6A, I _B = 30mA		3.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 4A; V _{CE} = 4V		2.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 60V, I _E = 0		0.2	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = 30V, I _B = 0		0.5	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0		5	mA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 4V	500		
h _{FE-2}	DC Current Gain	I _C = 4A; V _{CE} = 4V	1000	15000	